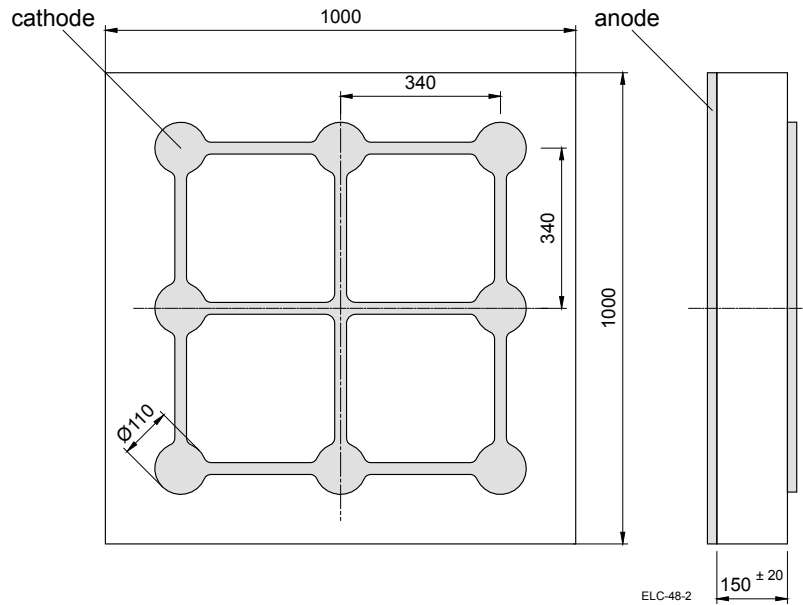


Radiation	Type	Technology	Electrodes
Infrared	Power chip, solder able	AlGaAs/GaAlAs	N (cathode) up

Outline (dimensions in microns)



Optical and Electrical Characteristics*

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F = 300 mA	V _F		1.5	2.0	V
Reverse voltage	I _R = 10 µA	V _R	5			V
Radiant power*	I _F = 300 mA	Φ _e	75	100		mW
Peak wavelength	I _F = 300 mA	λ _p	860	875	890	nm
Spectral bandwidth at 50%	I _F = 300 mA	Δλ _{0.5}		45		nm
Switching time	I _F = 300 mA	t _r , t _f		25		ns

*Chip packaged on TO-46 header covered with epoxy, in cylindrical copper heatsink

Labeling

Type	Lot N°	Φ _e (typ, min, max)	Quantity
ELC-870-29-2			

Packing: Chips on adhesive film with wire-bond side on top